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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/718,896	11/20/2003	Yung-Chang Lin	JCLA11793	1665
23900	7590	05/04/2007	EXAMINER	
J C PATENTS, INC. 4 VENTURE, SUITE 250 IRVINE, CA 92618			VU, DAVID	
		ART UNIT	PAPER NUMBER	
		2818		
		MAIL DATE	DELIVERY MODE	
		05/04/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary	Application No.	Applicant(s)	
	10/718,896	LIN ET AL.	
	Examiner	Art Unit	
	DAVID VU	2818	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 11/27/06.
- 2a) This action is **FINAL**. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 13-17, 25-34 and 36-43 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) Claim(s) _____ is/are allowed.
- 6) Claim(s) 13-17, 25-34 and 36-43 is/are rejected.
- 7) Claim(s) _____ is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on 20 November 2003 is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|---|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date <u>03/07/07</u> | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

1. Claims 13-17, 25-34 and 36-43 are rejected under 35 U. S. C. 102(b) as being anticipated by Rajeevakumar (US Pat. 5,426,324).

Regarding claims 13, 14, 16, 17, 34-37 and 39-41, Rajeevakumar discloses in figs. 1, 8 and 13 a trench capacitor, comprising: a substrate 1 having a trench; a conducting layer 11 filling trench; a first capacitor dielectric layers 10/31 between a surface of trench and conducting 11, wherein the first capacitor dielectric layer 10/31 continuously extends from inside the trench to an upper surface of the substrate (fig. 6); a protruding electrode 2 on substrate 1 around trench and covering a junction of trench and substrate 1; a second capacitor dielectric layer 4a (fig. 8) between conducting layer 11 and substrate 1, substrate 1 around first and second capacitor dielectric layers 10/4a being a bottom electrode; and a conducting structure electrically 8 (col. 2, lines 43-58) connecting protruding electrode 2 and conducting layer 11, wherein conducting layer 11, protruding electrode 2, and conducting structure 8 serve as an upper electrode, and

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wherein conducting structure 8 electrically connecting protruding electrode 2 by contacting the upper surface of protruding electrode 2 (fig. 1).

Regarding claims 25, 26, 28, 29, Rajeevakumar discloses a dynamic random access memory cell, comprising: a substrate 1 having a trench; a conducting layer 11 filling trench; a first capacitor dielectric layer 10/31 between the surface of trench and conducting layer 11, wherein the first capacitor dielectric layer 10/31 continuously extends from inside the trench to an upper surface of the substrate (fig. 6); a protruding electrode 2 on substrate 1 around trench and covering a junction of trench and substrate 1; a second capacitor dielectric layer 4a between conducting layer 11 and substrate 1, substrate 1 around first and second capacitor dielectric layers 10/4a being a bottom electrode; a gate electrode 2 on substrate 1 beside protruding electrode 2; a plurality of drain/source regions 13 in substrate beside two sides of gate electrode 2; a gate dielectric layer 4a between gate electrode 2 and substrate 1; and a conducting structure 8 electrically connecting protruding electrode 2 (fig. 1) and conducting layer 11, and conducting layer 11, protruding electrode 2, and conducting structure 8 (col. 2, lines 43-58) being an upper electrode, and wherein conducting structure 8 electrically connecting protruding electrode 2 by contacting the upper surface of protruding electrode 2 (fig. 1).

Regarding claims 15, 27, 32, 33 and 38, Rajeevakumar discloses capacitor dielectric layer comprises: a first portion 10 (col. 3, lines 8-27 and 58-65) between the surface of trench and conducting layer 11; and a second portion 4a (col. 4, line 27) between conducting layer 11 and substrate 1 (fig. 8).

Regarding claims 30 and 42, Rajeevakumar discloses a plurality of spacers 4 on sidewalls of conducting layer 2 and gate electrode 2 (fig 8)

Regarding claims 31 and 43, Rajeevakumar discloses a self-aligned silicide layer 14 on surfaces of conducting layer 11 and gate electrode 2 (fig. 1).

Response to Arguments

2. Applicant's arguments with respect to the pending claims have been considered but are moot in view of the new ground(s) of rejection. Although the same reference is applied (Rajeevakumar), the rejections are based on a new interpretation of that reference. Therefore, the arguments presented in response to the interpretation used in the previous Office Action are no longer applicable.

Conclusion

3. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a). A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be

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calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Vu whose telephone number is (571) 272-1798. The examiner can normally be reached on Monday-Friday from 8:00am to 5:00pm. If attempt to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith S can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR, Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



DAVID VU
PRIMARY EXAMINER